

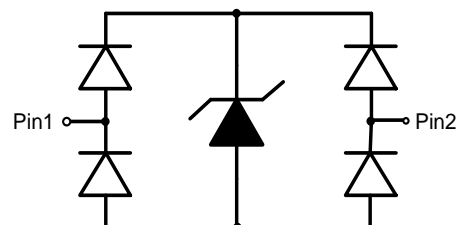
Descriptions

The ESD5311N is an ultra-low capacitance TVS (Transient Voltage Suppressor) designed to protect high speed data interfaces. It has been specifically designed to protect sensitive electronic components which are connected to data and transmission lines from over-stress caused by ESD (Electrostatic Discharge).

The ESD5311N incorporates one pair of ultra-low capacitance steering diodes plus a TVS diode.

The ESD5311N may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact discharge) according to IEC61000-4-2, and withstand peak pulse current up to 4A (8/20 μs) according to IEC61000-4-5.

The ESD5311N is available in DFN1006-2L package. Standard products are Pb-free and Halogen-free.



Features

- Stand-off voltage: 5V Max
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 20\text{kV}$ (contact discharge) IEC61000-4-5 (surge): 4 A (8/20 μs)
- Ultra-low capacitance: $C_J = 0.25\text{pF}$ typ.
- Ultra-low leakage current: $I_R < 1\text{nA}$ typ.
- Low clamping voltage: $V_{CL} = 21\text{V}$ typ. @ $I_{PP} = 16\text{A}$ (TLP)
- Solid-state silicon technology

Applications

- USB 2.0 and USB 3.0
- HDMI 1.3 and HDMI 1.4
- SATA and eSATA
- DVI
- IEEE 1394
- PCI Express
- Portable Electronics
- Notebooks

Absolute maximum ratings

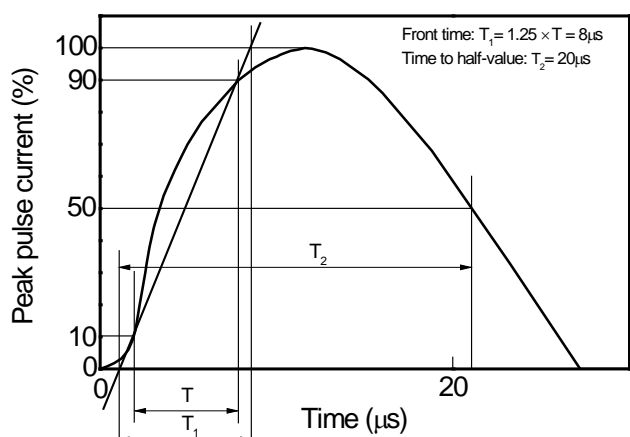
Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu\text{s}$)	P_{pk}	84	W
Peak pulse current ($t_p = 8/20\mu\text{s}$)	I_{PP}	4	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	
Operation junction temperature	T_J	125	$^{\circ}\text{C}$
Lead temperature	T_L	260	$^{\circ}\text{C}$
Storage temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

Electrical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)

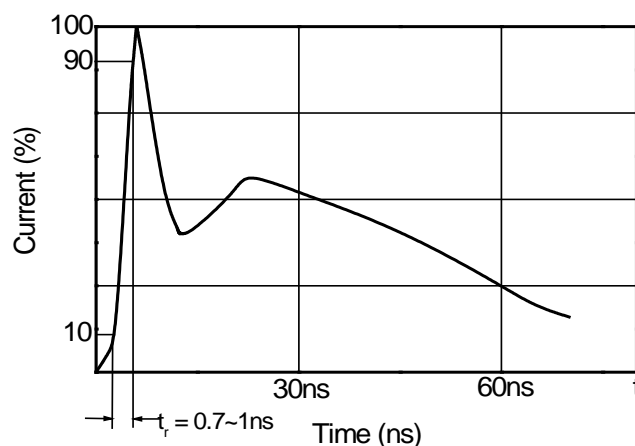
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5\text{V}$		<1	100	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1\text{mA}$	7.5	9.0	10.0	V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16\text{A}$, $t_p = 100\text{ns}$		21.0		V
Dynamic resistance ¹⁾	R_{DYN}			0.7		Ω
Clamping voltage ²⁾	V_{CL}	$V_{ESD} = 8\text{kV}$		21		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1\text{A}$, $t_p = 8/20\mu\text{s}$			14	V
		$I_{PP} = 4\text{A}$, $t_p = 8/20\mu\text{s}$			21	V
Junction capacitance	C_J	$V_R = 0\text{V}$, $f = 1\text{MHz}$ Any I/O pin to GND		0.25	0.4	pF

- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

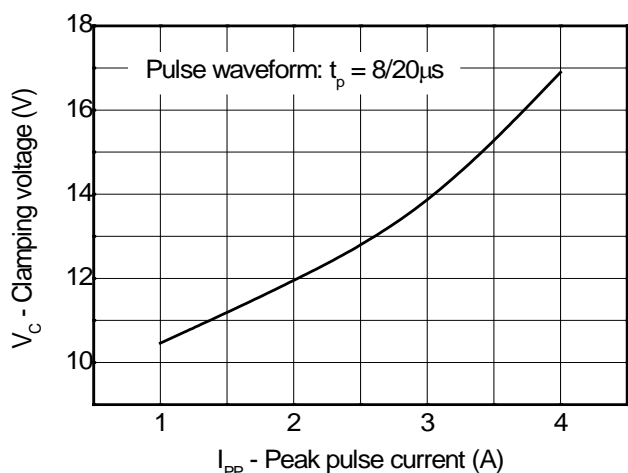
Typical characteristics ($T_A=25^{\circ}\text{C}$, unless otherwise noted)



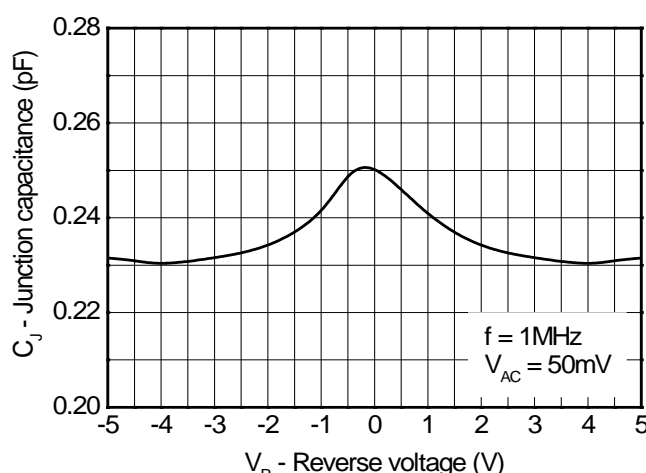
8/20 μs waveform per IEC61000-4-5



Contact discharge current waveform per IEC61000-4-2

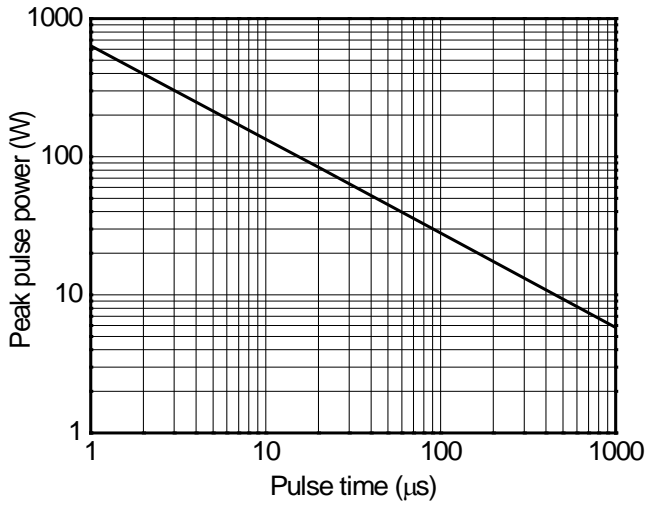


Clamping voltage vs. Peak pulse current

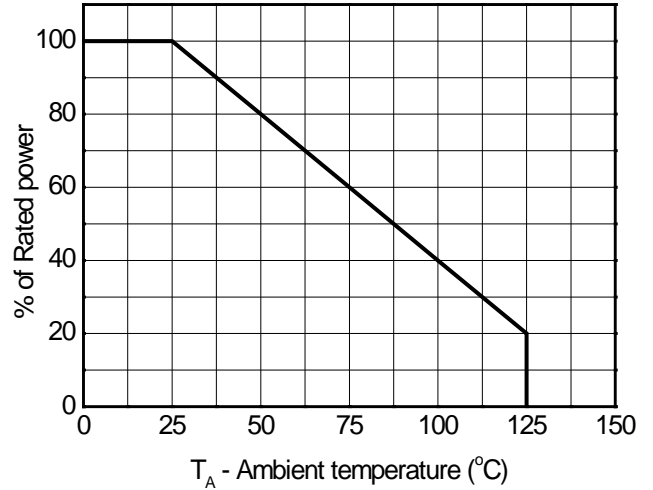


Capacitance vs. Reverses voltage

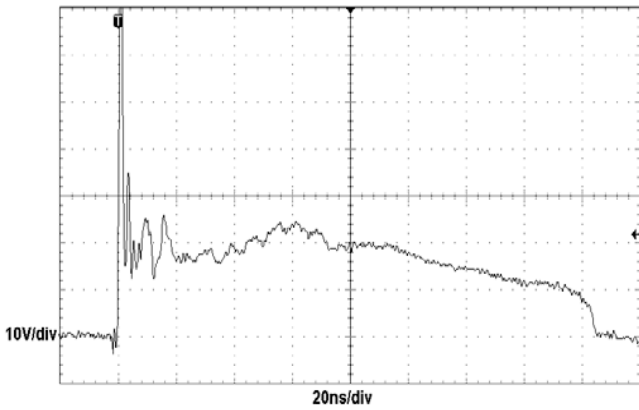
Typical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)



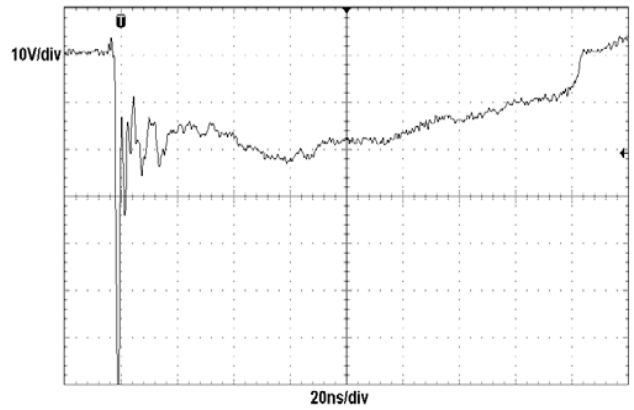
Non-repetitive peak pulse power vs. Pulse time



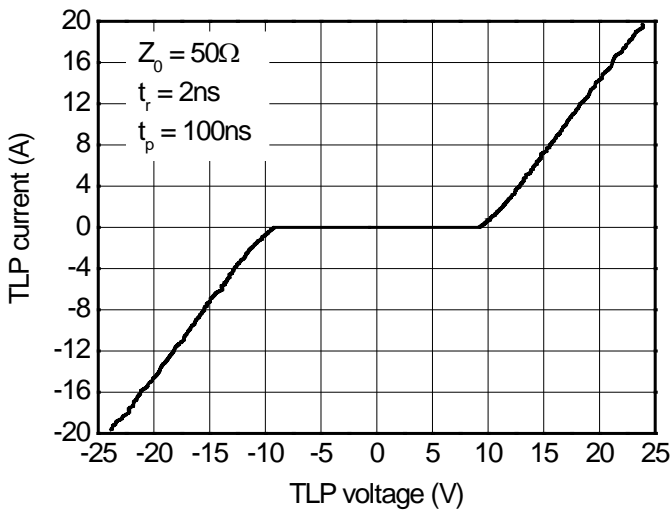
Power derating vs. Ambient temperature



ESD clamping
(+8kV contact discharge per IEC61000-4-2)

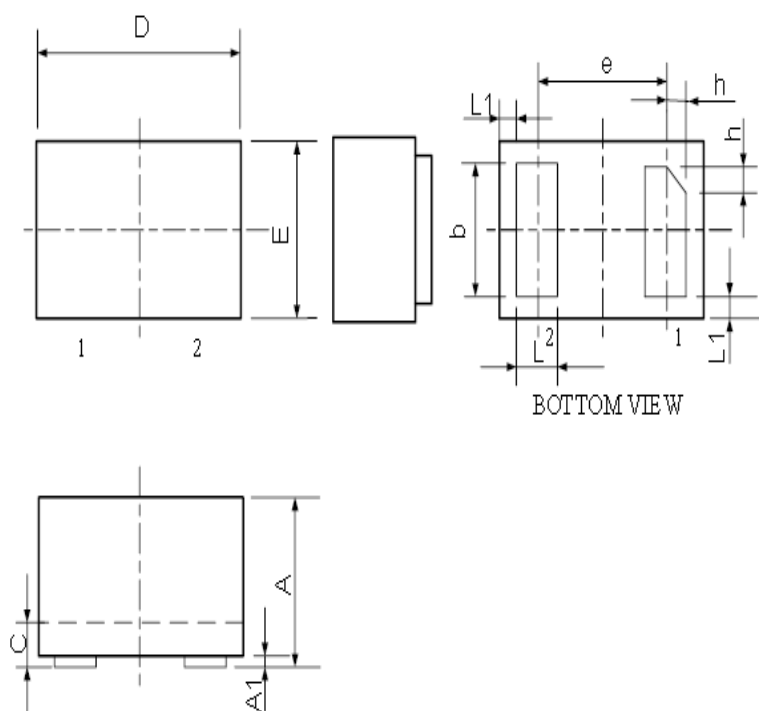


ESD clamping
(-8kV contact discharge per IEC61000-4-2)



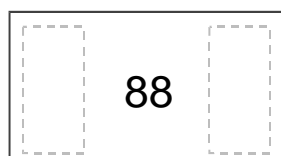
TLP Measurement

DFN1006-2 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Minimum	Maximum
A	0.450	0.550
A1	0.000	0.050
b	0.45	0.55
C	0.12	0.18
D	0.950	1.050
e	0.65BSC	
E	0.550	0.650
L	0.200	0.300
L1	0.05REF	
h	0.07	0.17

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW ESD5311N	DFN1006-2	10000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)